TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)

Complementary Silicon Plastic Power Transistors

Designed for use in general purpose amplifier and switching applications.

Features

- High Current Gain − Bandwidth Product
- Compact TO−220 Package
- These Devices are Pb−Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	V_{CEO}	 40 60 80 100	Vdc
Collector−Base Voltage TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	V_{CB}	 40 60 80 100	Vdc
Emitter−Base Voltage	V_{EB}	5.0	Vdc
Collector Current − Continuous	I_C	3.0	Adc
Collector Current − Peak	I_{CM}	5.0	Adc
Base Current	I_B	1.0	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	 40 0.32	 W W/°C
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	 2.0 0.016	 W W/°C
Unclamped Inductive Load Energy (Note 1)	E	32	mJ
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. I_C = 1.8 A, L = 20 mH, P.R.F. = 10 Hz, V_{CC} = 10 V, R_{BE} = 100 Ω

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	3.125	°C/W

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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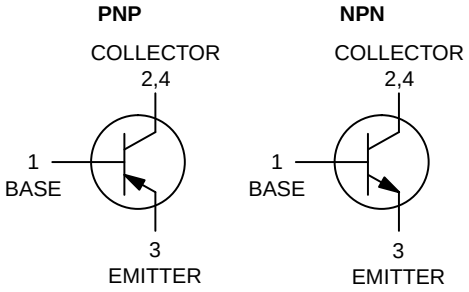
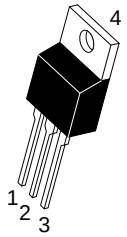
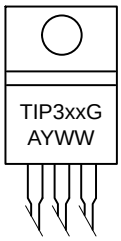
3 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 40−60−80−100 VOLTS, 40 WATTS





TO−220
CASE 221A
STYLE 1

MARKING DIAGRAM



TIP3xx	= Device Code
xx	= 1, 1A, 1B, 1C, 2, 2A, 2B, 2C,
A	= Assembly Location
Y	= Year
WW	= Work Week
G	Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Sustaining Voltage (Note 2) (I_C = 30 mAdc, I_B = 0) TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	$V_{CEO(sus)}$	 40 60 80 100	 − − − −	Vdc
Collector Cutoff Current (V_{CE} = 30 Vdc, I_B = 0) TIP31G, TIP32G, TIP31AG, TIP32AG (V_{CE} = 60 Vdc, I_B = 0) TIP31BG, TIP31CG, TIP32BG, TIP32CG	I_{CEO}	 − −	 0.3 0.3	mAdc
Collector Cutoff Current (V_{CE} = 40 Vdc, V_{EB} = 0) TIP31G, TIP32G (V_{CE} = 60 Vdc, V_{EB} = 0) TIP31AG, TIP32AG (V_{CE} = 80 Vdc, V_{EB} = 0) TIP31BG, TIP32BG (V_{CE} = 100 Vdc, V_{EB} = 0) TIP31CG, TIP32CG	I_{CES}	 − − − −	 200 200 200 200	μAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	I_{EBO}	−	1.0	mAdc
ON CHARACTERISTICS (Note 2)				
DC Current Gain (I_C = 1.0 Adc, V_{CE} = 4.0 Vdc) (I_C = 3.0 Adc, V_{CE} = 4.0 Vdc)	h_{FE}	 25 10	 − 50	−
Collector−Emitter Saturation Voltage (I_C = 3.0 Adc, I_B = 375 mAdc)	$V_{CE(sat)}$	−	1.2	Vdc
Base−Emitter On Voltage (I_C = 3.0 Adc, V_{CE} = 4.0 Vdc)	$V_{BE(on)}$	−	1.8	Vdc
DYNAMIC CHARACTERISTICS				
Current−Gain − Bandwidth Product (I_C = 500 mAdc, V_{CE} = 10 Vdc, f_{test} = 1.0 MHz)	f_T	3.0	−	MHz
Small−Signal Current Gain (I_C = 0.5 Adc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	20	−	−

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

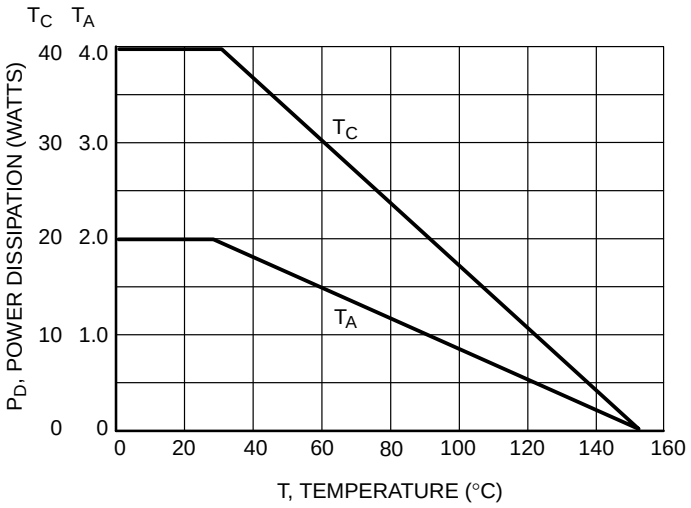
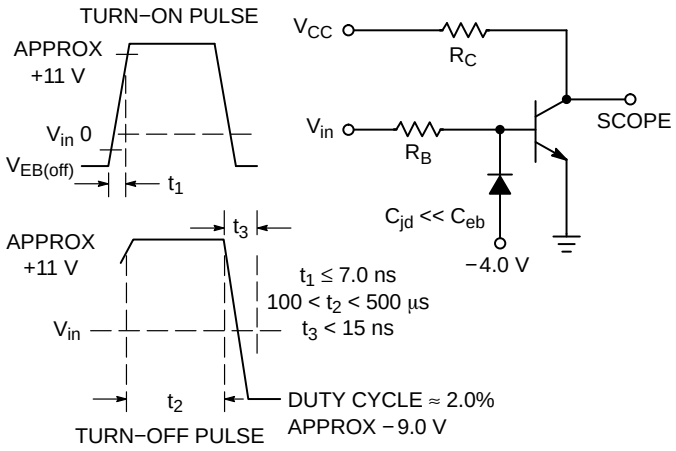


Figure 1. Power Derating



R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS.

Figure 2. Switching Time Equivalent Circuit

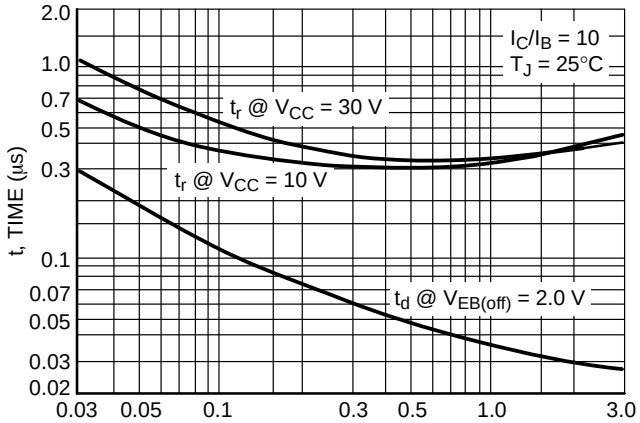


Figure 3. Turn−On Time

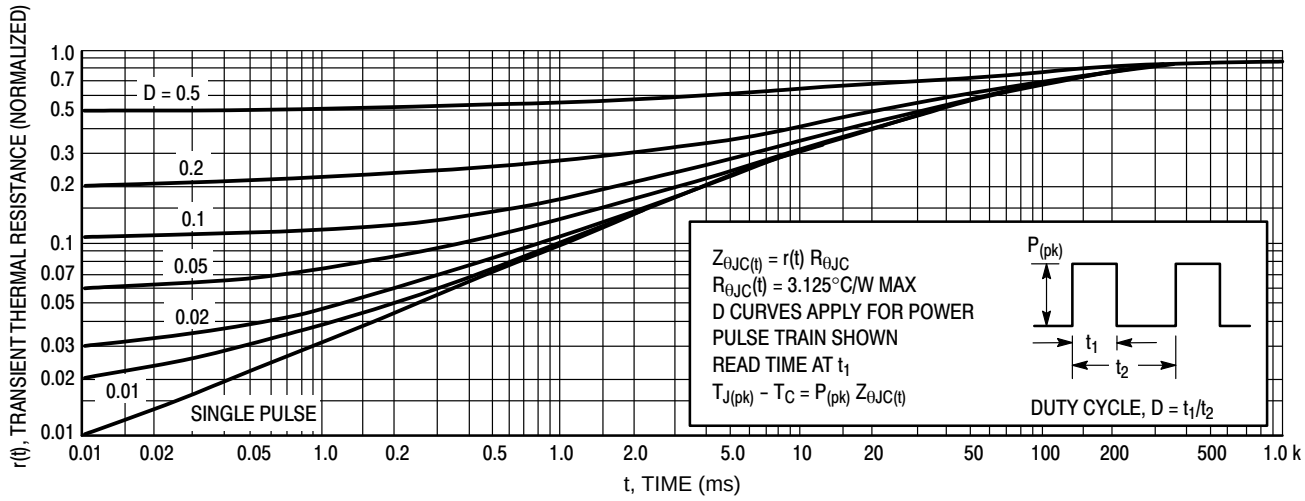


Figure 4. Thermal Response

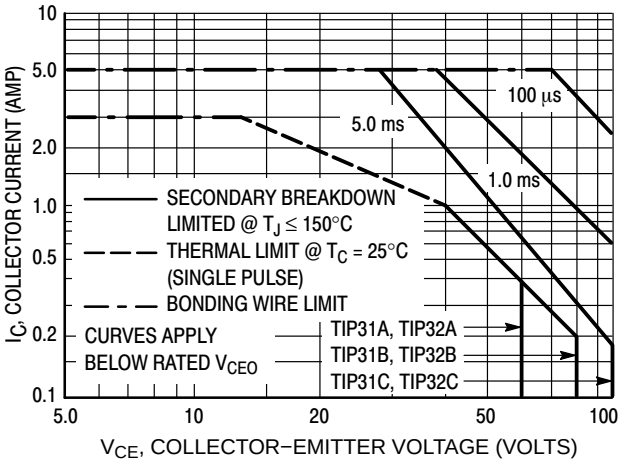


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150°C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150°C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

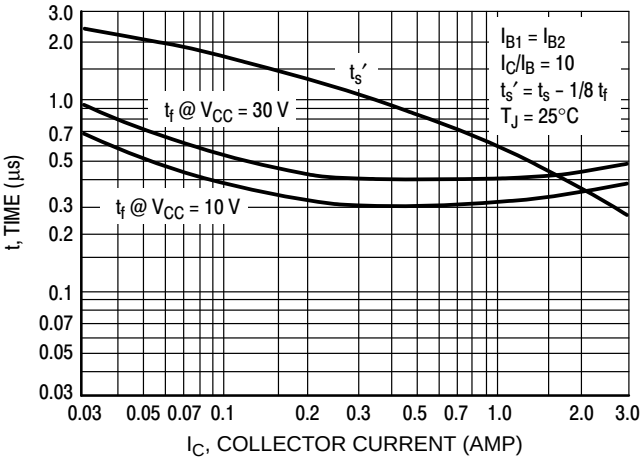


Figure 6. Turn−Off Time

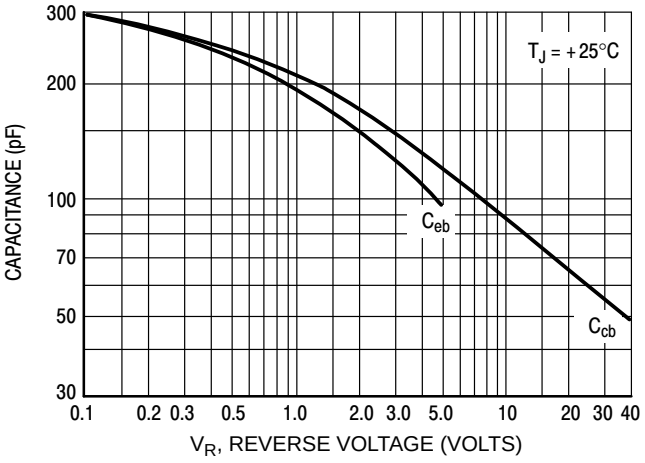


Figure 7. Capacitance

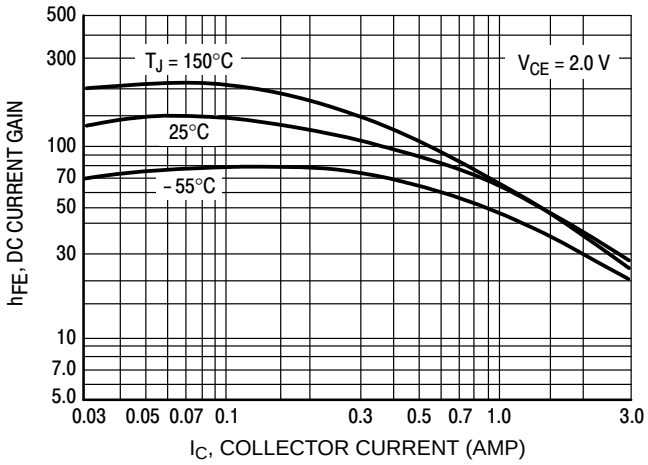


Figure 8. DC Current Gain

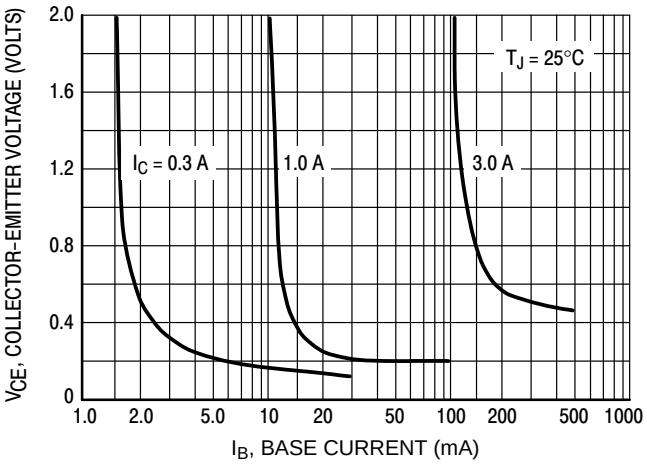


Figure 9. Collector Saturation Region

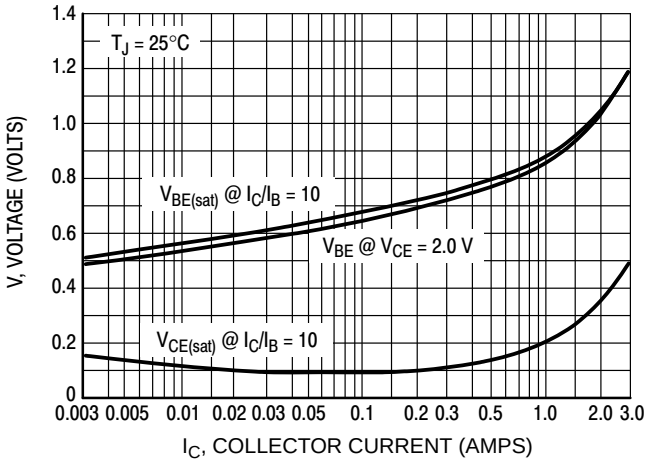


Figure 10. “On” Voltages

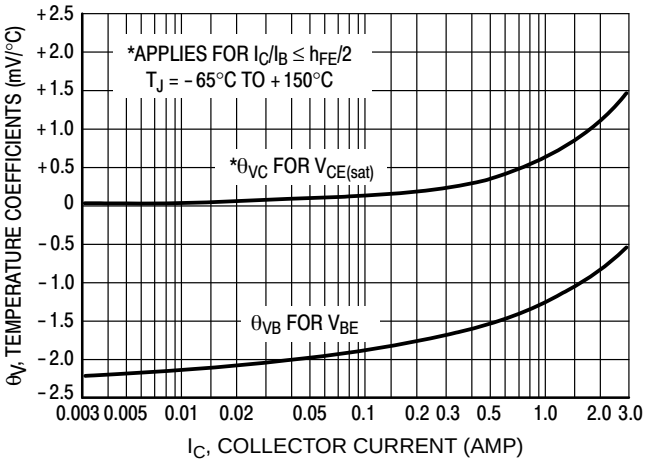


Figure 11. Temperature Coefficients

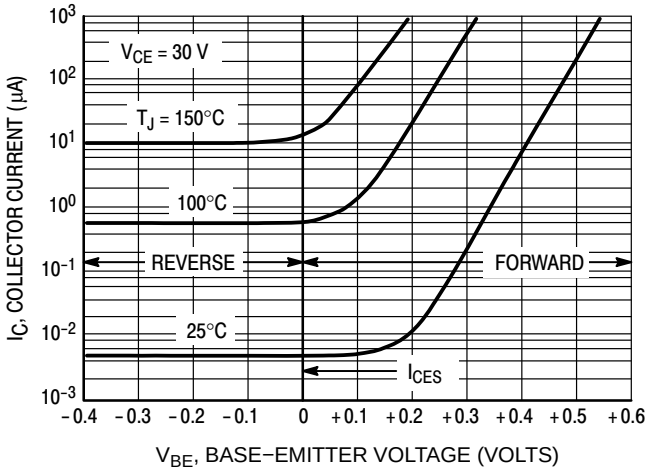


Figure 12. Collector Cut−Off Region

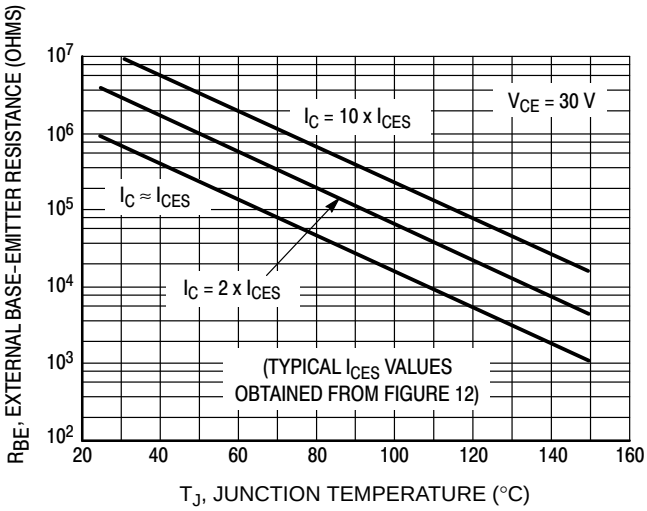


Figure 13. Effects of Base−Emitter Resistance

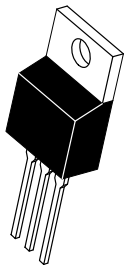
ORDERING INFORMATION

Device	Package	Shipping
TIP31G	TO−220 (Pb−Free)	50 Units / Rail
TIP31AG	TO−220 (Pb−Free)	50 Units / Rail
TIP31BG	TO−220 (Pb−Free)	50 Units / Rail
TIP31CG	TO−220 (Pb−Free)	50 Units / Rail
TIP32G	TO−220 (Pb−Free)	50 Units / Rail
TIP32AG	TO−220 (Pb−Free)	50 Units / Rail
TIP32BG	TO−220 (Pb−Free)	50 Units / Rail
TIP32CG	TO−220 (Pb−Free)	50 Units / Rail

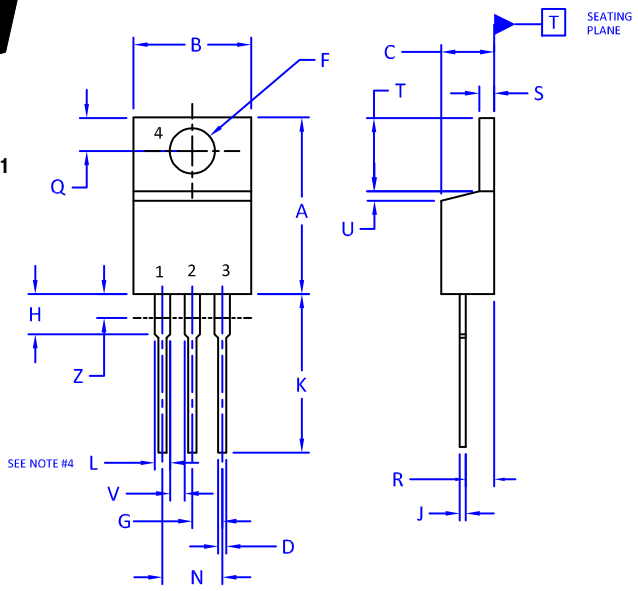
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

TO−220
CASE 221A
ISSUE AK

DATE 13 JAN 2022



SCALE 1:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	----	1.15	---
Z	----	0.080	---	2.04

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
4. EMITTER

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

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DESCRIPTION:	**TO−220**	**PAGE 1 OF 1**

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

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